

# **1.27-Gbps/pin, 3mW/pin Wireless Superconnect (WSC) Interface Scheme**

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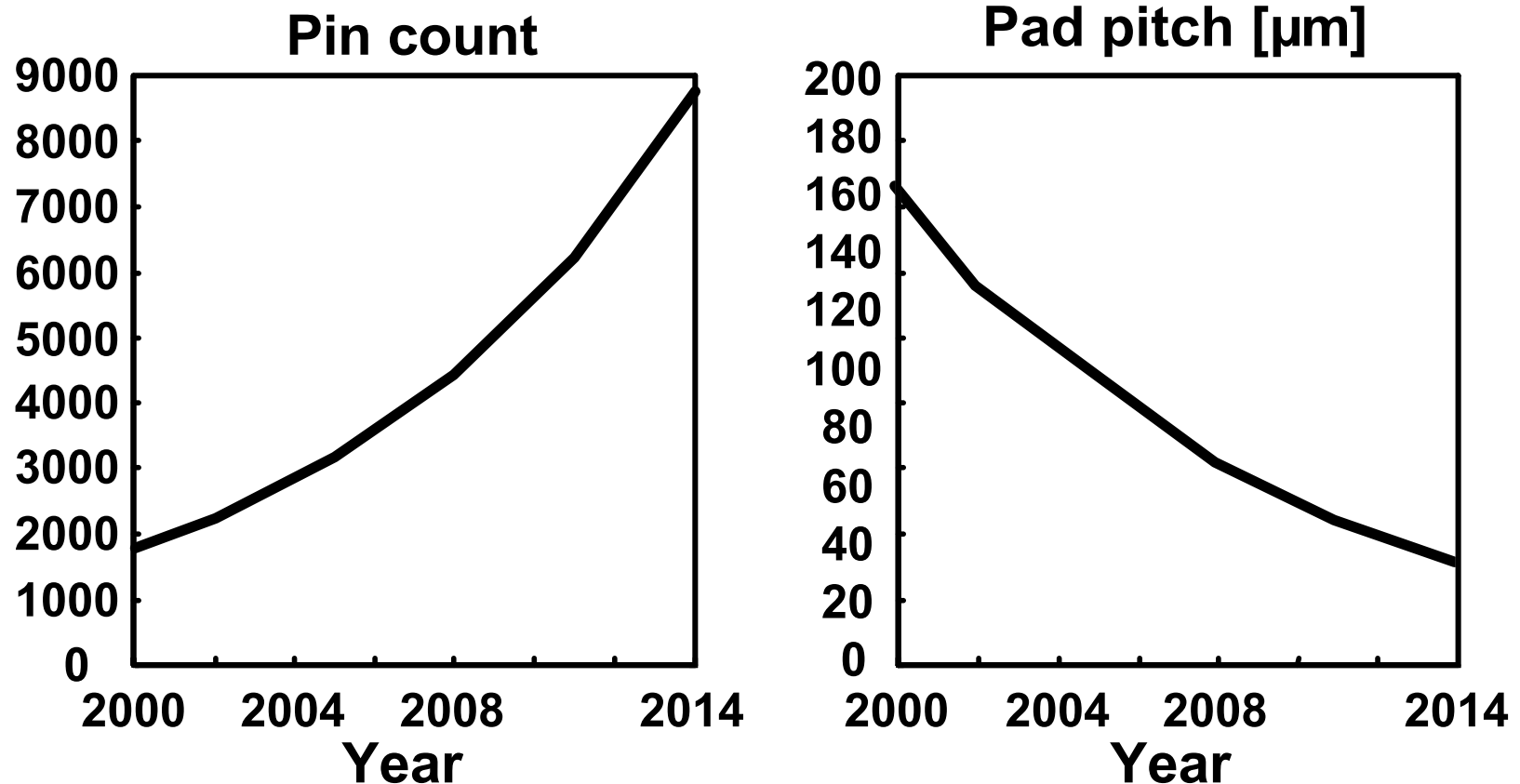
# Outline

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- **Background**
- **WSC scheme overview**
- **Circuit design**
- **Measurement**
- **Simulation**
- **Conclusion**

# Trend in assembly predicted by ITRS

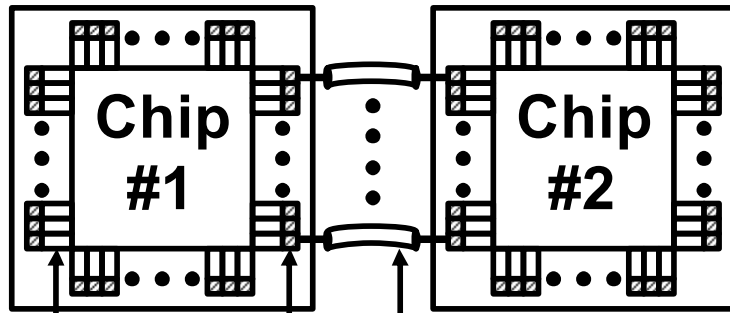
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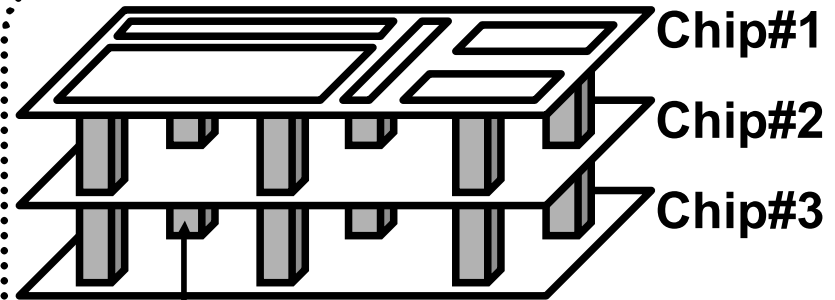
**Target: Power/pin = 10.0mW (70W for 7000 pins)**

**Pad pitch = 20μm (7000 pads in 2.8mm<sup>2</sup>)**

# Various existing I/O schemes

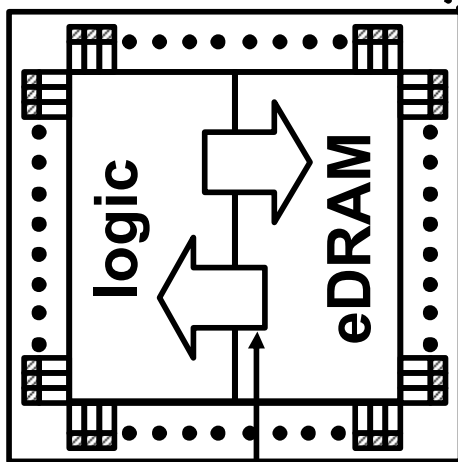


Buffer/ESD Pad PCB connection  
**(A) High-speed link**



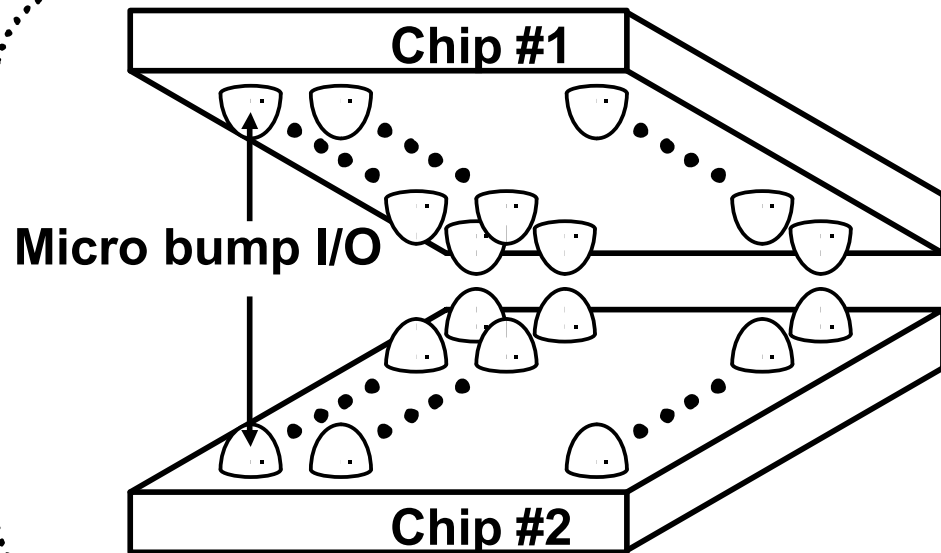
MEMS I/O

**(B) 3D MEMS**



On-chip bus

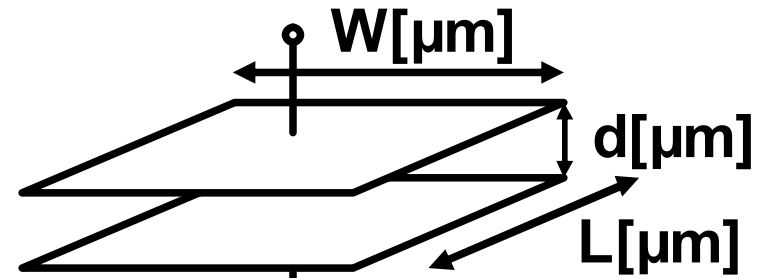
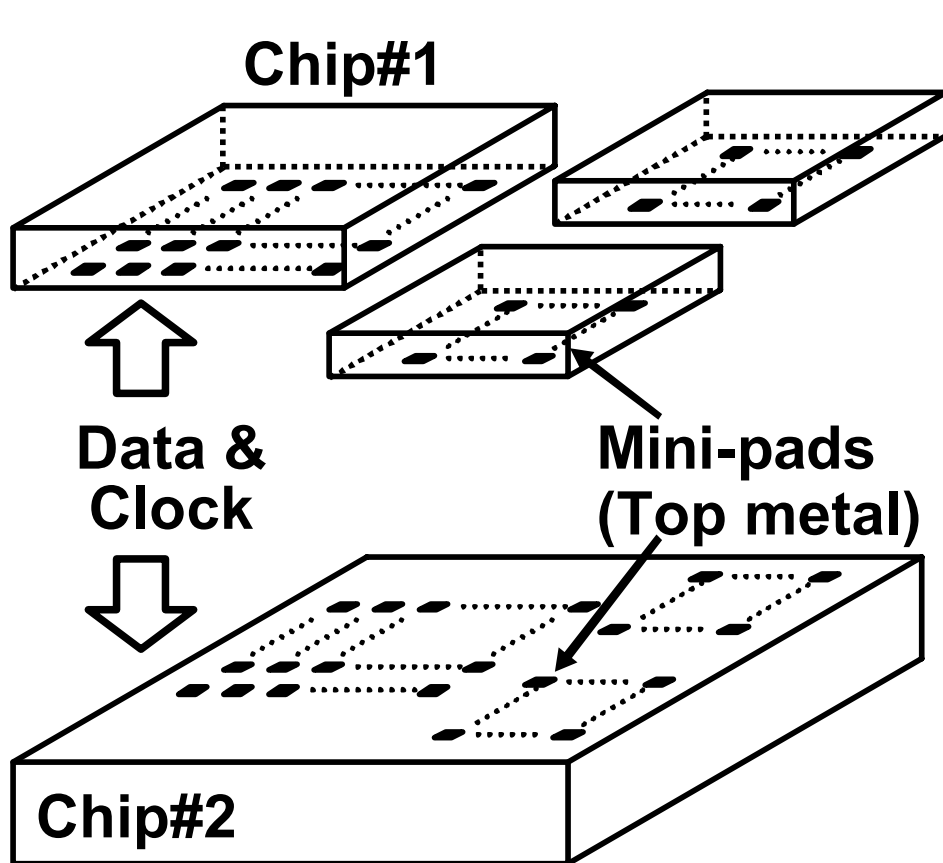
**(C) System on a chip**



Micro bump I/O

**(D) Micro bump**

# Wireless superconnect scheme overview



$$C = \frac{\epsilon \cdot L \cdot W}{d}$$

$$\epsilon_{\text{SiO}_2} = 35 \times 10^{-18} [\text{F}/\mu\text{m}]$$

<ex.>

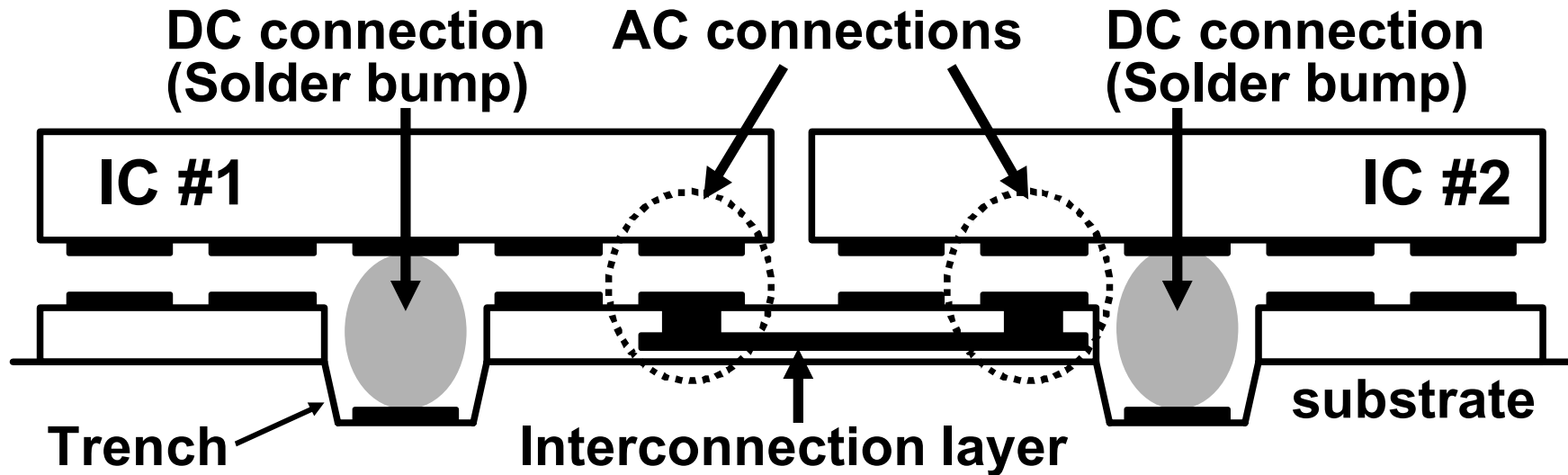
(L, W, d) (in  $\mu\text{m}$ )

(10, 10, 1)  $\Rightarrow$  C=3.5fF

(20, 20, 1)  $\Rightarrow$  C=14.0fF

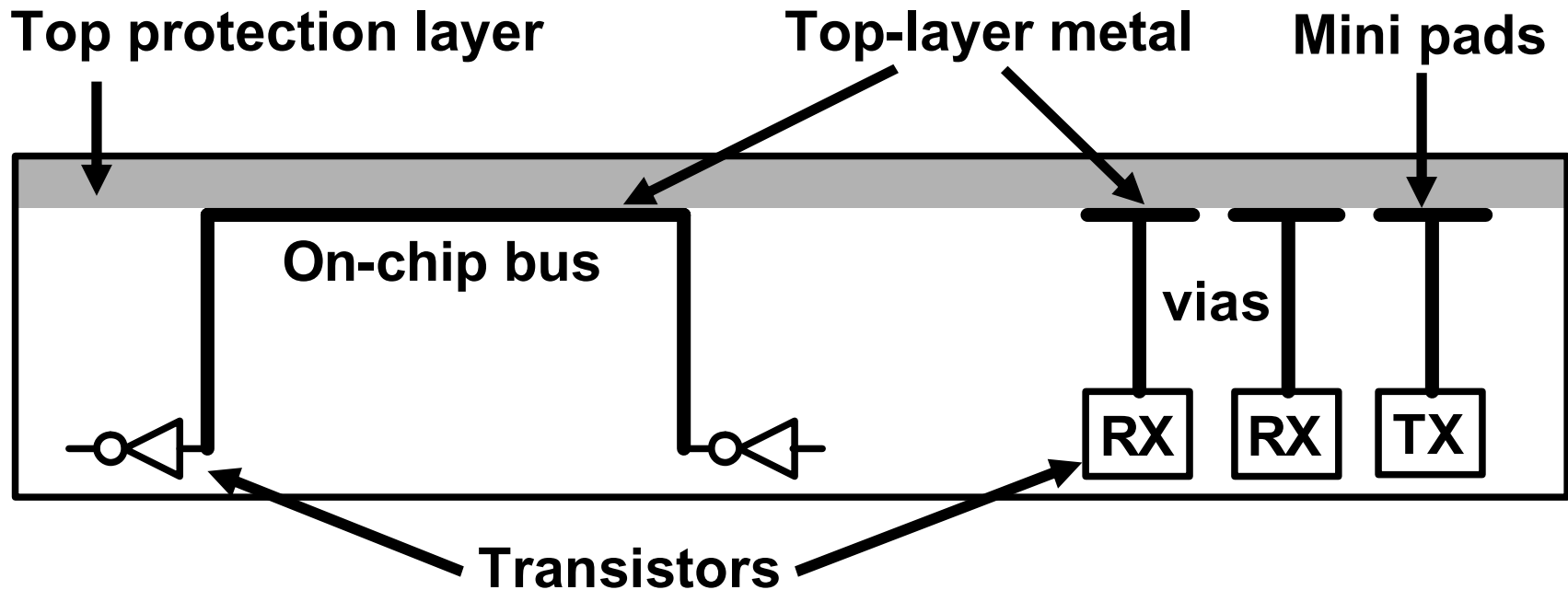
# Previous work

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**S. Mick et al. "4Gbps High-Density AC Coupled Interconnection," Custom Integrated Circuits Conf., 2002, pp.133-140. (North Carolina State University)**

# ESD in WSC



**ESD resiliency of pads**

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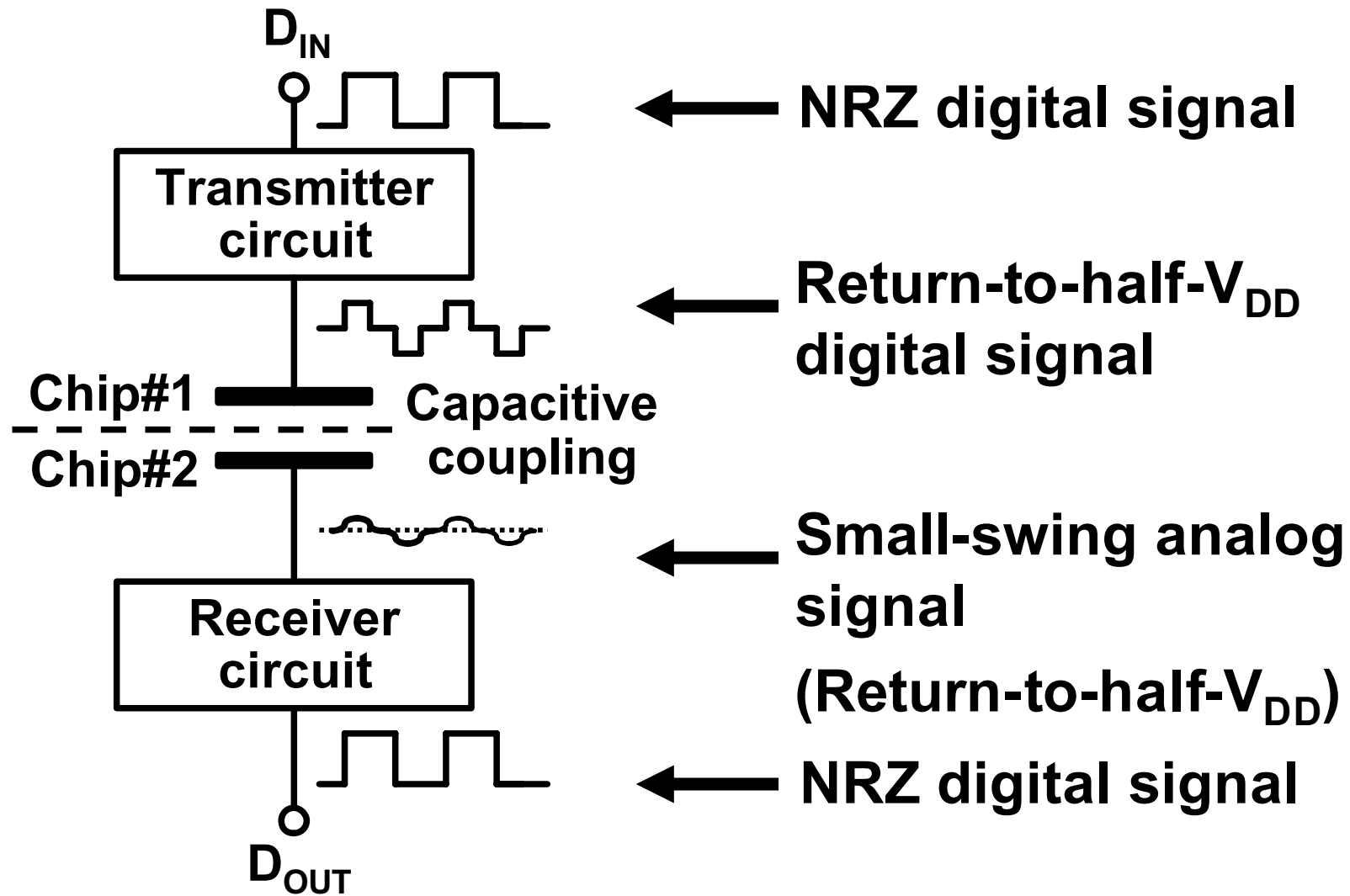
**ESD resiliency of on-chip interconnections**

# Comparison of interface schemes

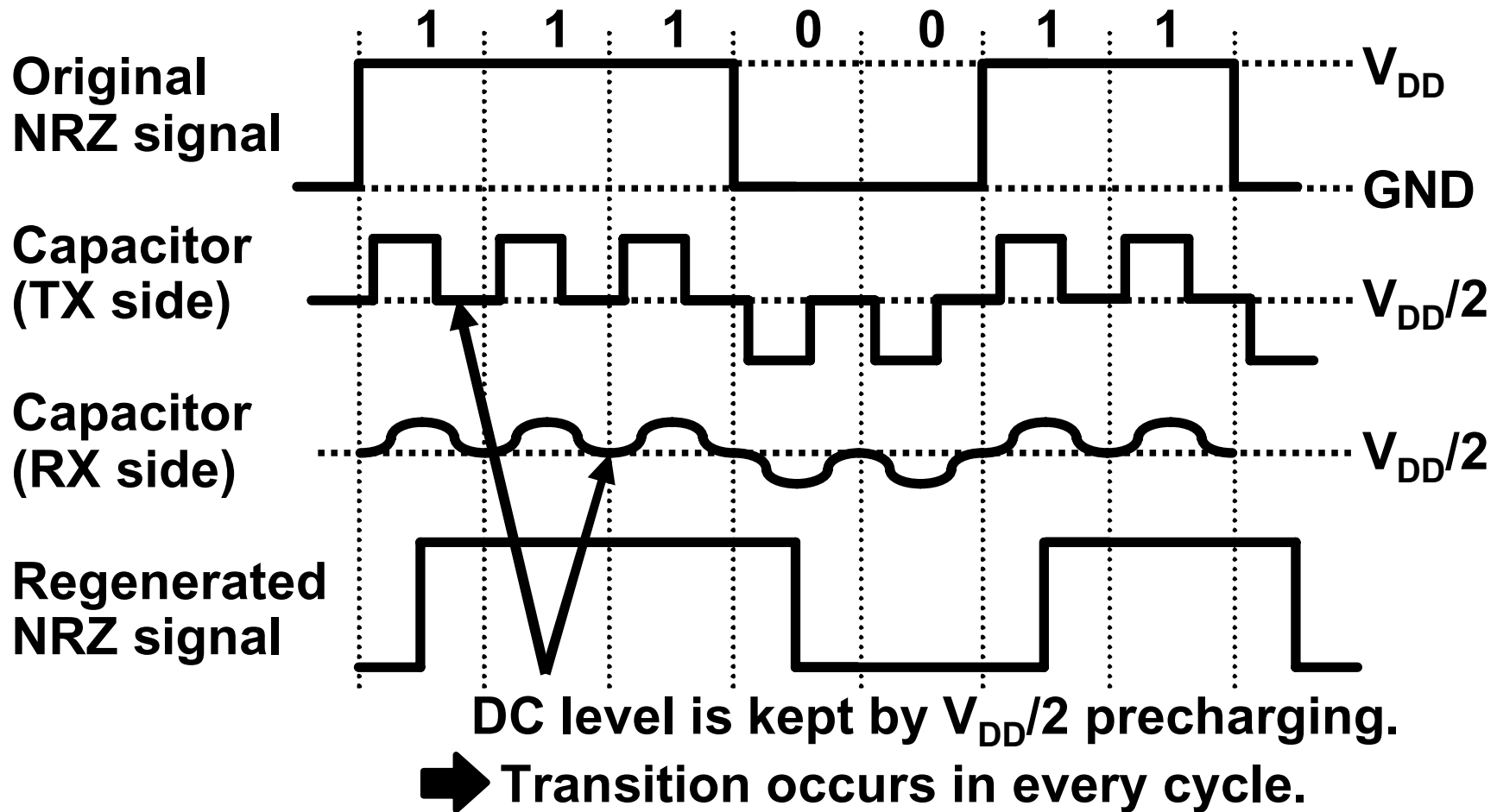
	Serial link	3D MEMS	SOC	$\mu$ bump	WSC
Bandwidth	-	+	++	+	+
Cost	+	--	-	+	++
Area	--	++	-	+	+
ESD	-	-	-	-	+
Power	--	+	++	+	+
TAT	-	--	--	+	++



# Signaling method in WSC

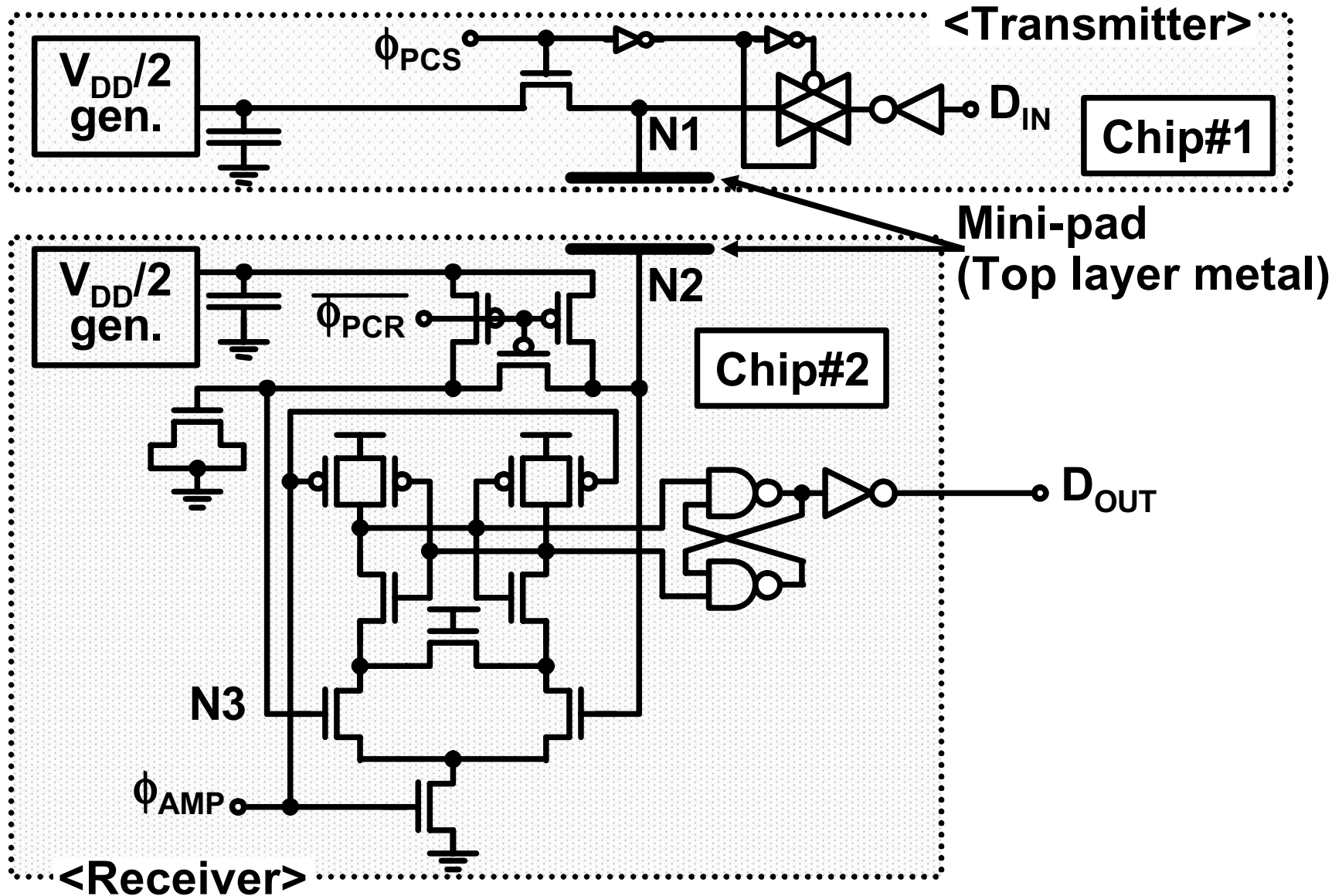


# No DC-wandering problem

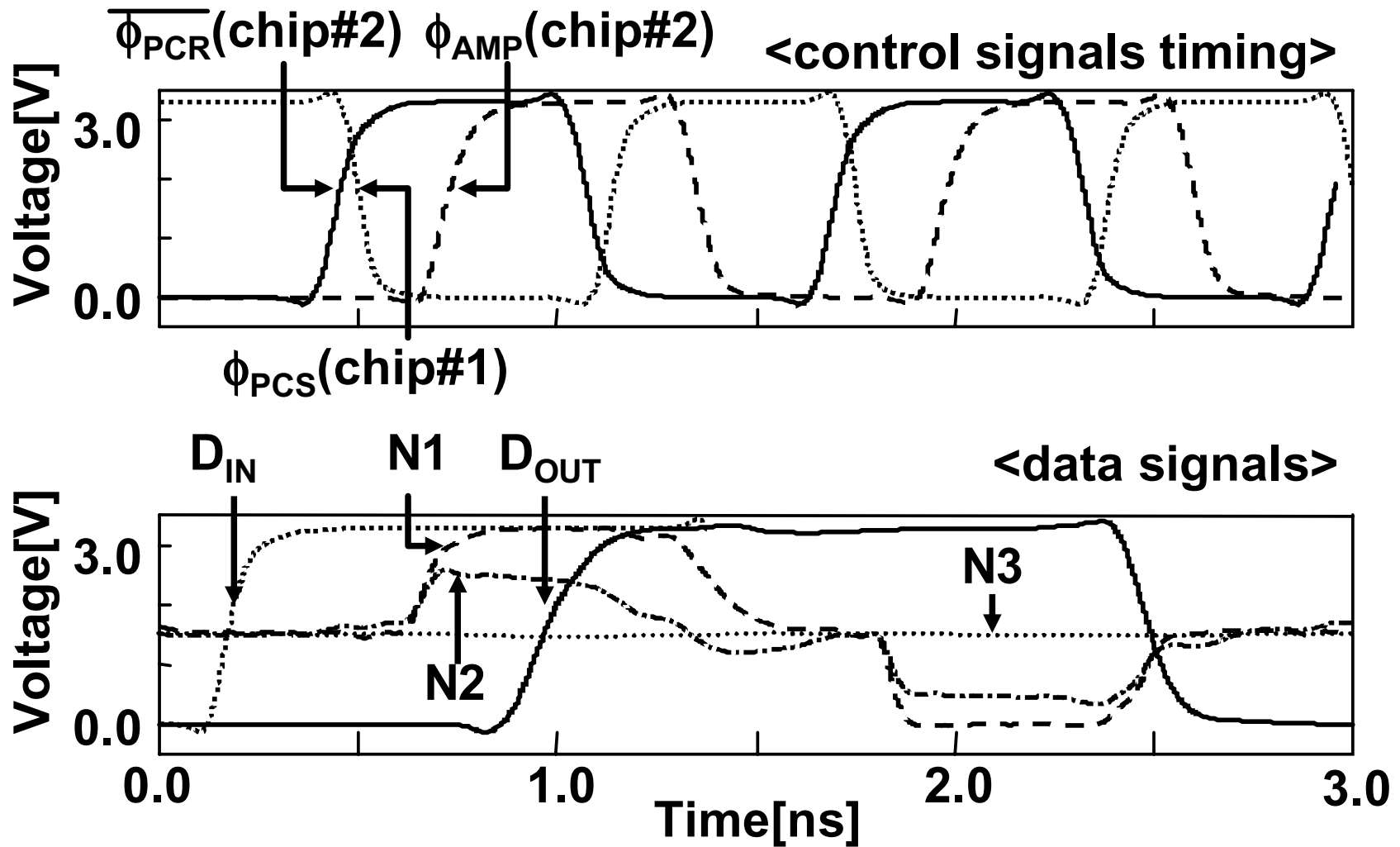


**Precise timing for precharging and amplifier activation is needed.**

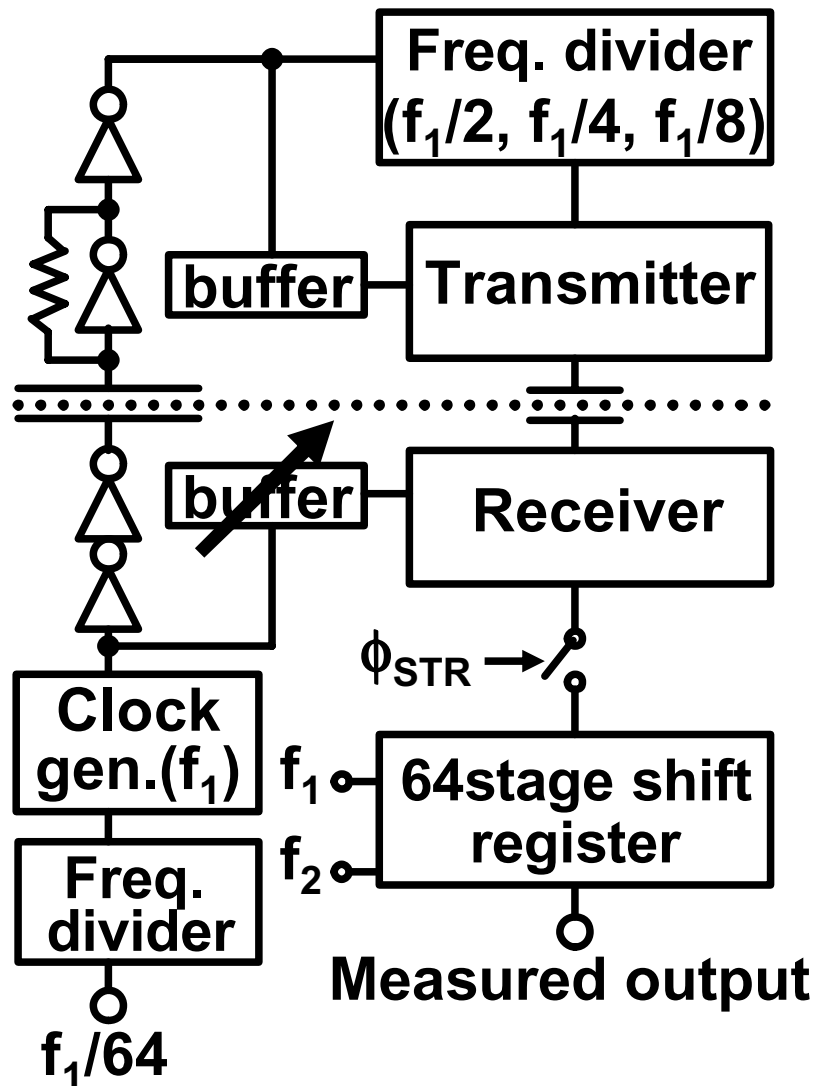
# Circuit diagram of transmitter and receiver



# Operating waveform



# Test environment



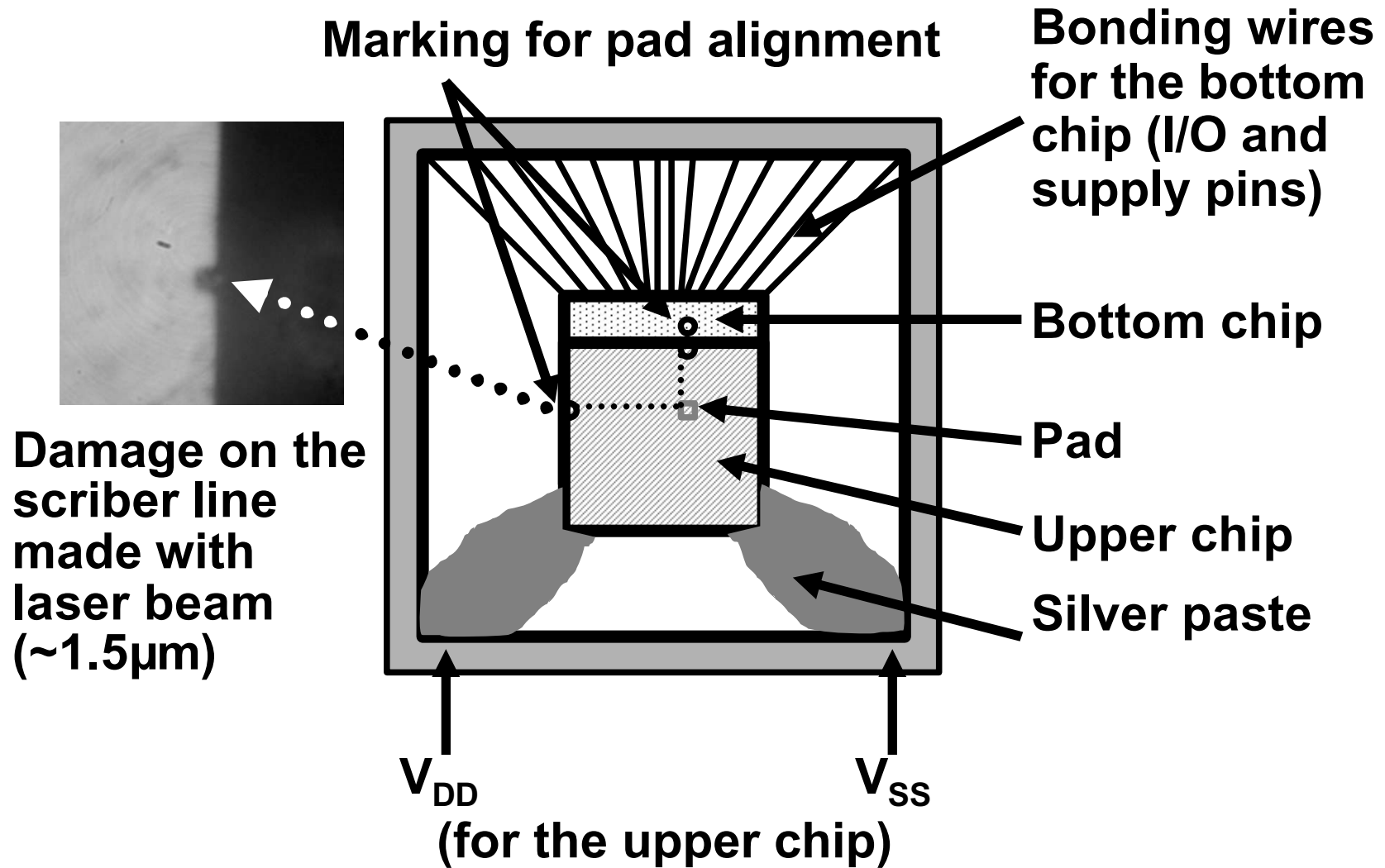
■ On-die clock generation for high frequency

■ Receiver timing control with a variable delay buffer

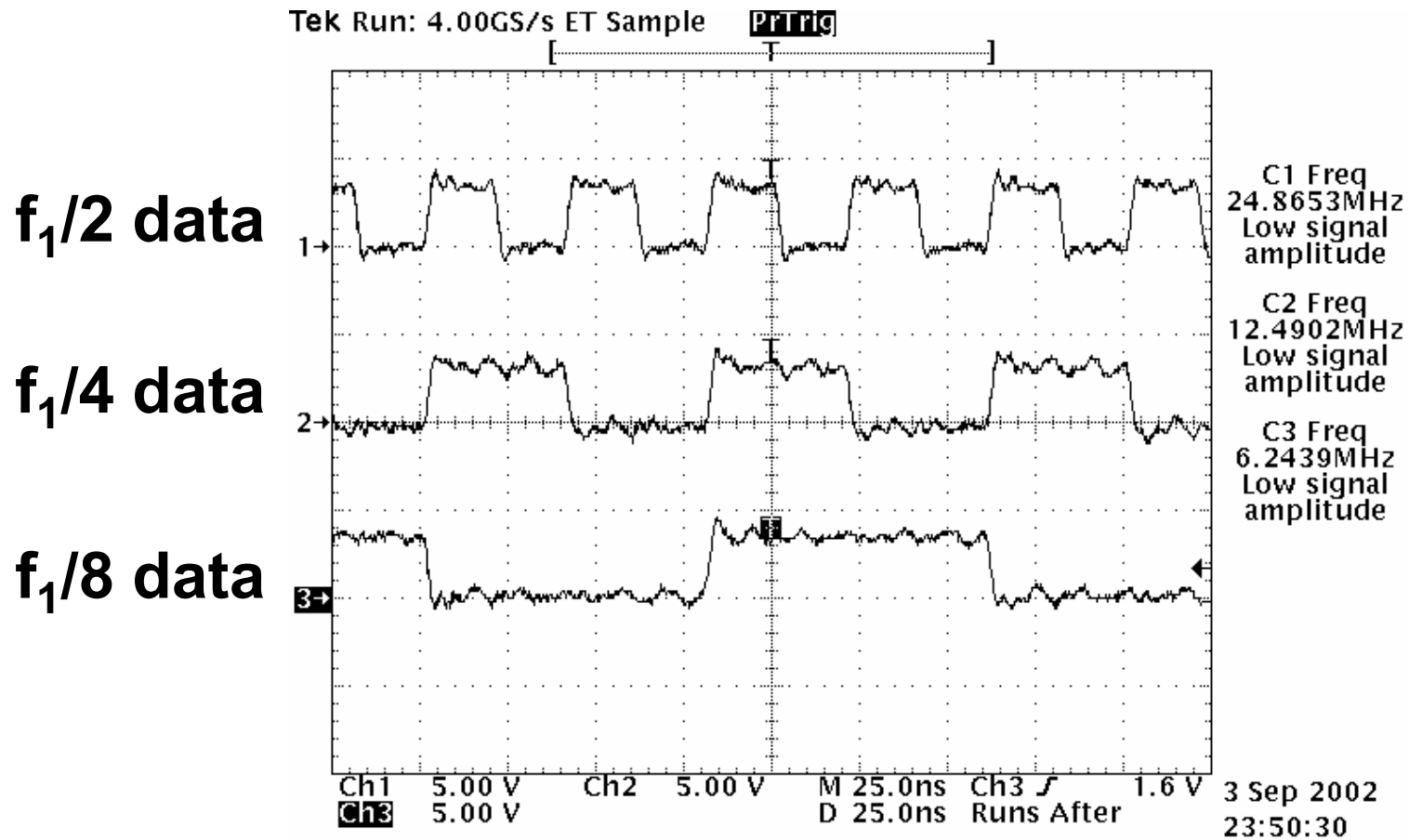
■ Monitoring clock frequency with a divider

■ Storing data sequences in a shift register

# Measurement setup

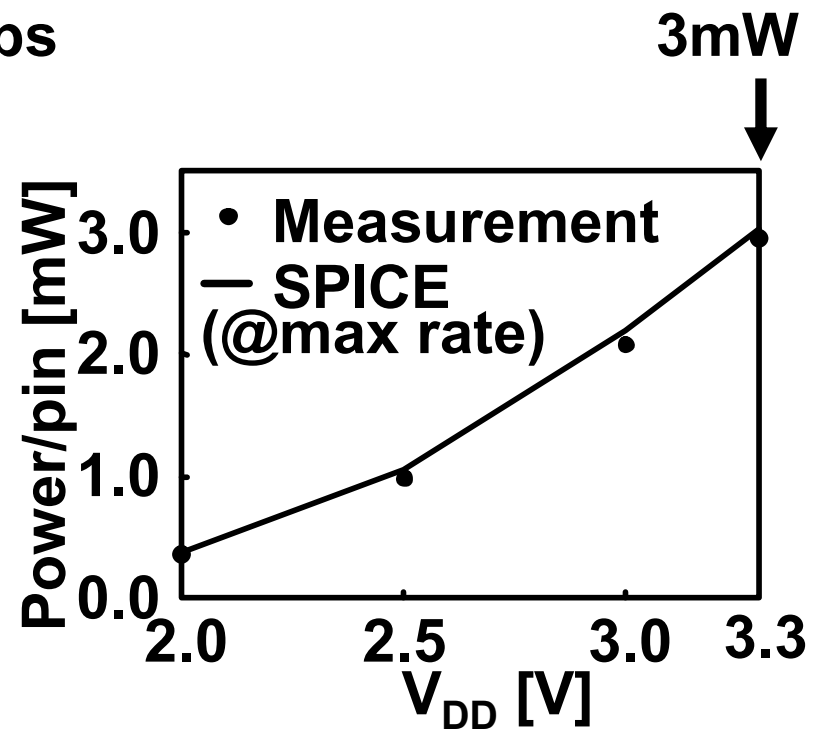
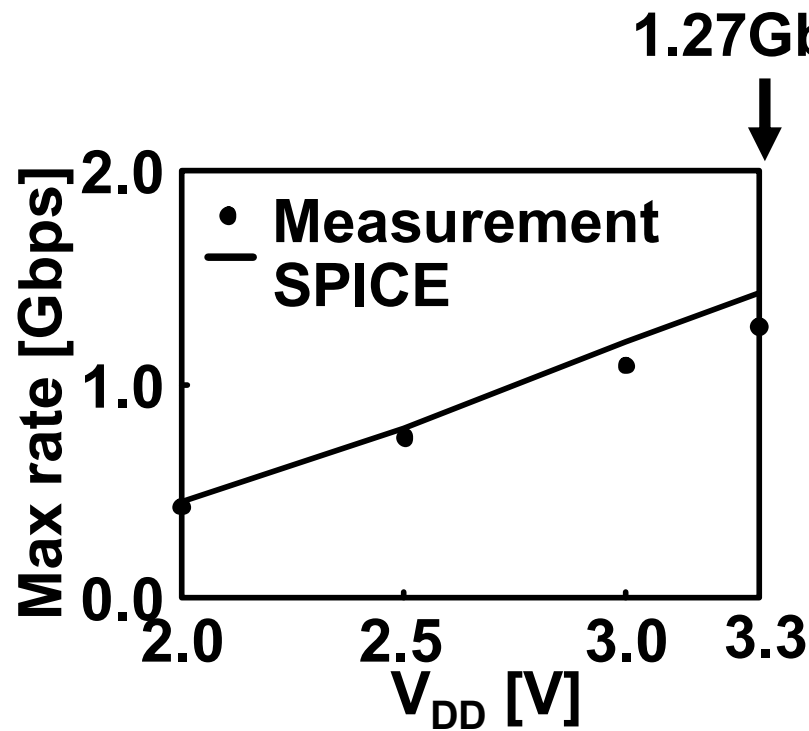


# Measured waveform



**$f_1 \sim 1\text{GHz}$  (scan-in),  $f_2 = 50\text{MHz}$  (scan-out)**

# Measured and simulated WSC performance



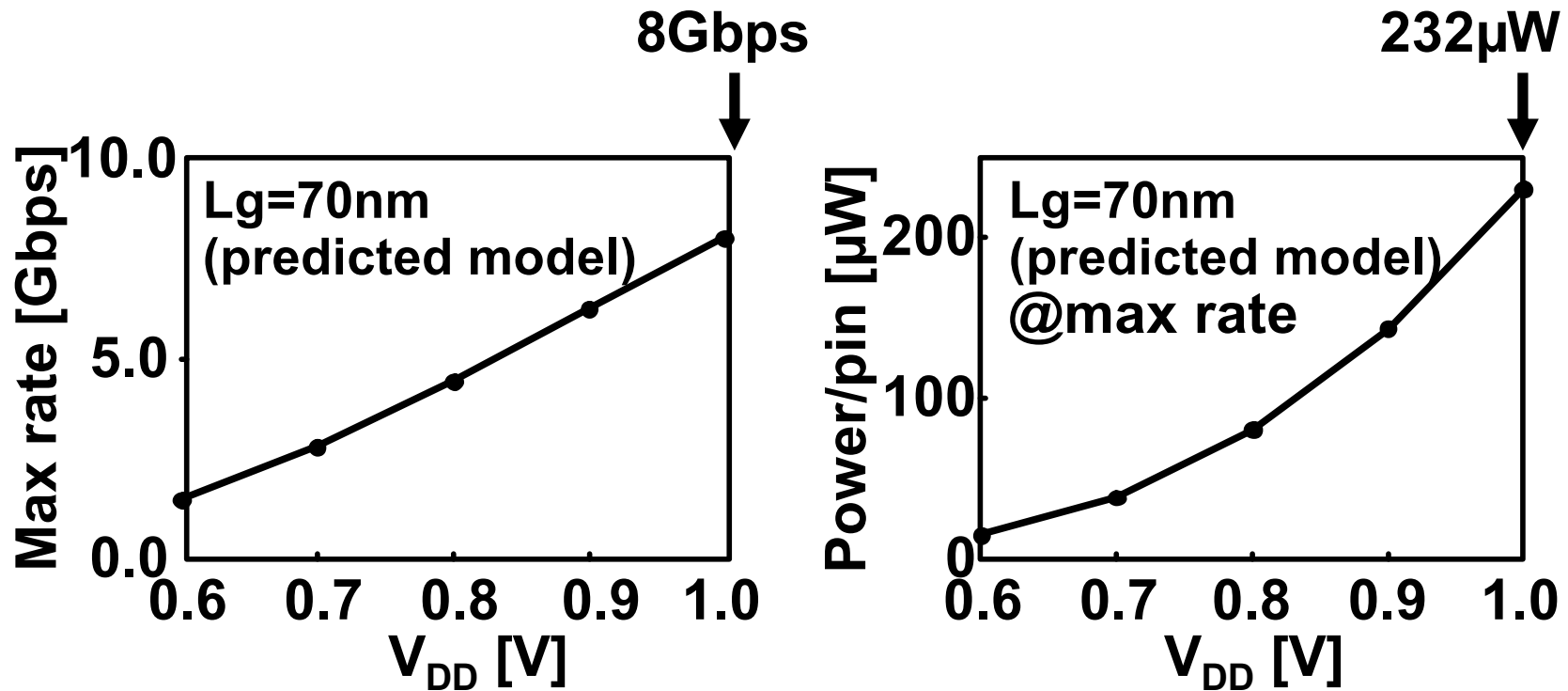
Transmitter : 360 $\mu$ A

Receiver : 540 $\mu$ A



# Simulated WSC performance in 70nm tech.

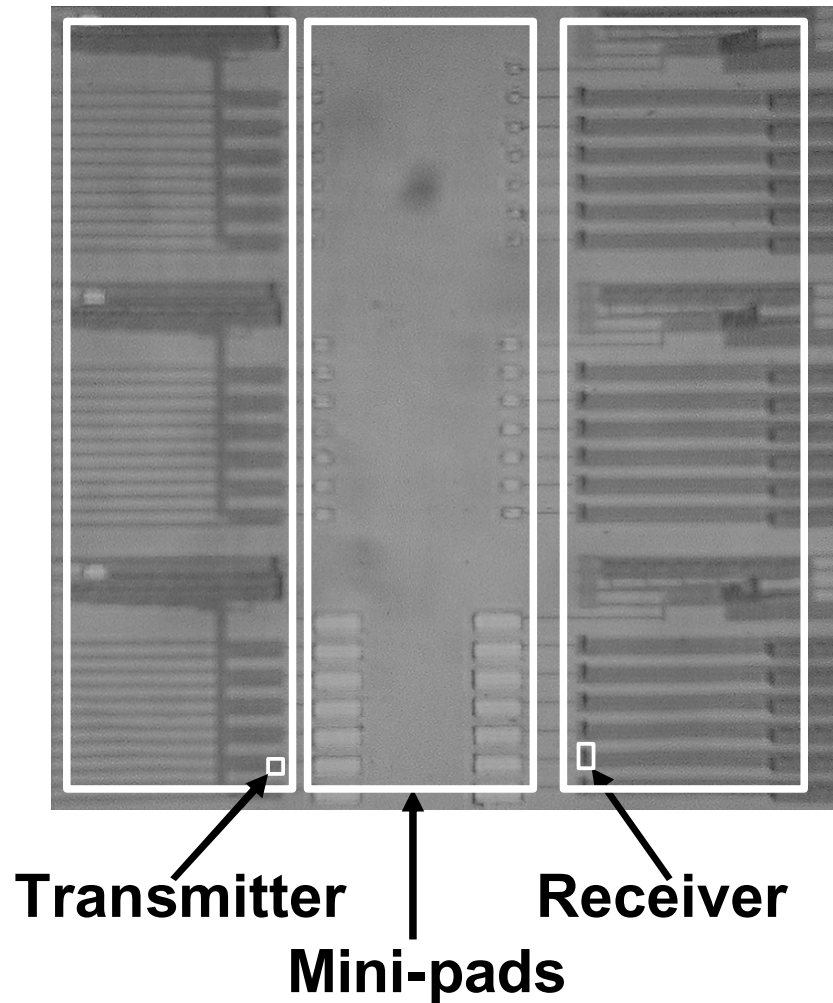
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**Future 7000 I/O pads can operate at 8GHz with only 1.63W.**

# Test chip microphotograph

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## Technology

**0.35 $\mu\text{m}$  CMOS**

**Triple metal**

**3.3V supply**

## I/O design

**Transmitter: 20 $\mu\text{m}$ X20 $\mu\text{m}$**

**Receiver: 12 $\mu\text{m}$ X12 $\mu\text{m}$**

**Pad: 10 $\mu\text{m}$ X20 $\mu\text{m}$**

# Conclusion

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- **WSC interface is proposed for high-density and low-power chip-to-chip communications.**
- **Low I/O capacitive load is achieved by small pad size and elimination of ESD structure.**
- **1.27-Gbps with 3mW from 3.3V power supply was measured in 0.35 $\mu$ m CMOS technology.**
- **Simulation results in 70nm technology show possibility of 7000 I/O pads operating at 8-Gbps with 1.63W in 2.82mm<sup>2</sup>.**

# Acknowledgements

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**Mr. Hiroyuki Hara and Mr. Tetsuya Fujita  
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for chip fabrication support**

**(VDEC = VLSI Design and Education Center)**